

# Filling the gap of silicon nitride photonic platform functionalities using micro-transfer printing

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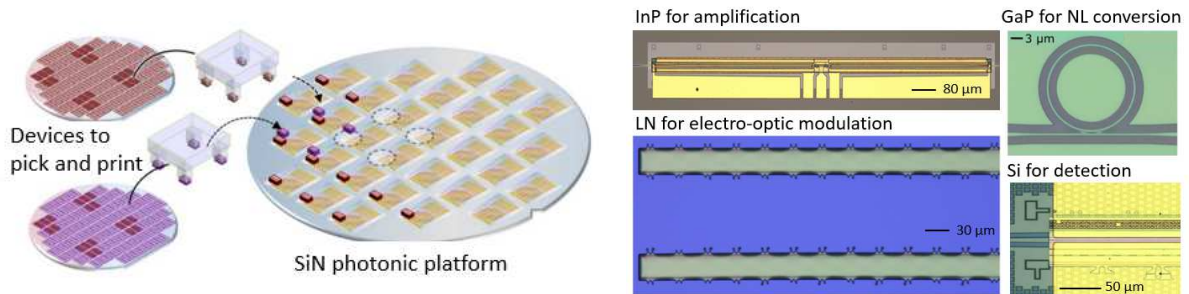
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**Keywords:** Integrated photonics, heterogeneous integration, micro-transfer printing

Photonic integrated circuits enable the miniaturization of key optical functions. Silicon (Si) and silicon nitride (SiN) photonic platforms have proven their maturity based on their compatibility with CMOS technology, giving rise to low cost, compact and scalable optical systems on a chip. Furthermore, in the case of SiN, the wide transparency window extends across the visible and near-infrared spectral regions, making it a strong candidate for numerous applications, including telecom/datacom, quantum technologies and bio-sensing. However, the SiN photonic platform lacks some important functionalities such as optical amplification, modulation, detection and intrinsic second order nonlinear frequency conversion. A versatile solution is to heterogeneously integrate devices, based on different materials, using the technique of micro-transfer printing [1] (Fig. 1). As such, diverse functionalities can be added to the SiN photonic platform at the back-end level to retain CMOS compatibility. In this presentation, we will discuss the remaining technological challenges such as SiN-to-device light coupling, wavelength compatibility, post-integration processing, limit of printed device sizes, multiple hetero-integration and scalability. Several recent device demonstrations (tab 1) are discussed to exemplify the current state-of-the-art and challenges.



**Figure - 1)** Illustration of devices hetero-integration on a SiN wafer via micro-transfer printing and microscope pictures of transfer printed devices

Property / functionality	SiN	Possible micro-transfer printed devices
Transparency window	0.25 to 5 $\mu\text{m}$	-
Propagation losses	0.01 to 0.1 dB/cm	-
Two-photon absorption	Negligible	-
Industry status	Low-volume production	-
Optical gain	Absent	InGaAs [2] / GaAs [3] / GaN [4] based amplifiers
Fast modulation	No Pockels, no carriers	Lithium niobate (LN) electro-optic modulators [5]
Nonlinear conversion	no intrinsic $\chi^{(2)}$ , $\chi^{(3)}$	PPLN [6] / GaP [7] ( $\chi^{(2)}$ and $\chi^{(3)}$ ) waveguides
Detection	No carriers	pin-Si photodiodes (slow) [8] / InGaAs UTC-photodiodes (fast) [9]

**Table 1)** Overview of the silicon nitride photonic platform properties and examples of micro-transfer printed devices adding new functionalities on the platform

## References

- [1] G. Roelkens *et al.*, Micro-transfer printing for heterogeneous Si photonic integrated circuits, IEEE Journal on Selected Topics in Quantum Electronics, 2022
- [2] S. Cuyvers, B. Haq, C. Op de Beeck, S. Poelman, A. Hermans, Z. Wang, A. Gocalinska, M. Ellamei, B. Corbett, G. Roelkens, K. Van Gasse, B. Kuyken, Low Noise Heterogeneous III-V-on-Silicon-Nitride Mode-Locked Comb Laser, Laser & Photonics Reviews, 2021
- [3] M. Kiewiet, S. Cuyvers, A. Hermans, M. Billet, J. Zhang, G. Roelkens, K. Van Gasse, B. Kuyken, Scalable Heterogeneous Integration of a Pre-Processed Facet-Emitting Visible-Wavelength GaAs Laser, accepted for publication in Conference on Lasers and Electro-Optics, United States, (to be published) 2023.
- [4] S. Poelman, M. Billet, A. Hermans, N. Fiuczek, H. Turski, B. Kuyken, Transfer Printing of InGaN/GaN Quantum-Well based Light Emitting Diodes, accepted for publication in Conference on Lasers and Electro-Optics, United States, (to be published) 2023.
- [5] T. Vanackere, T. Vandekerckhove, L. Bogaert, M. Billet, S. Poelman, S. Cuyvers, Joris Van Kerrebrouck, Arno Moerman, Olivier Caytan, Sam Lemey, Guy Torfs, G. Roelkens, S. Clemmen, B. Kuyken, High-Speed Lithium Niobate Modulator on Silicon Nitride using Micro-Transfer Printing, accepted for publication in Conference on Lasers and Electro-Optics, United States, (to be published) 2023
- [6] T. Vandekerckhove, T. Vanackere, J. De Witte, I. Luntadila Lufungula, E. Vissers, G. Roelkens, S. Clemmen, B. Kuyken, High-Efficiency Second Harmonic Generation in Heterogeneously-Integrated Periodically-Poled Lithium Niobate on Silicon Nitride, accepted for publication in Conference on Lasers and Electro-Optics Europe, Germany, (to be published) 2023
- [7] M. Billet, L.N Reis, Y. Leger, C. Cornet, F. Raineri, I. Sagnes, K. Pantzas, G. Beaudoin, G. Roelkens, F. Leo, B. Kuyken, Gallium phosphide-on-insulator integrated photonic structures fabricated using micro-transfer printing, Optical Materials Express, 2021
- [8] S. Cuyvers, A. Hermans, M. Kiewiet, J. Goyvaerts, G. Roelkens, K. Van Gasse, D. Van Thourhout, B. Kuyken, Heterogeneous integration of Si photodiodes on silicon nitride for near-visible light detection, Optics Letters, 2022
- [9] D. Maes, S. Lemey, G. Roelkens, M. Zaknourne, V. Avramovic, E. Okada, P. Sznitgiser, E. Peytavit, G. Ducournau, B. Kuyken, High-speed uni-traveling-carrier photodiodes on silicon nitride, APL Photonics, 2023